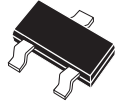




CMPT5401

**SURFACE MOUNT
PNP SILICON TRANSISTOR**



SOT-23 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5401 type is a PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage amplifier applications.

MARKING CODE: C2L

MAXIMUM RATINGS: (T_A=25°C)

Collector-Base Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Continuous Collector Current	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

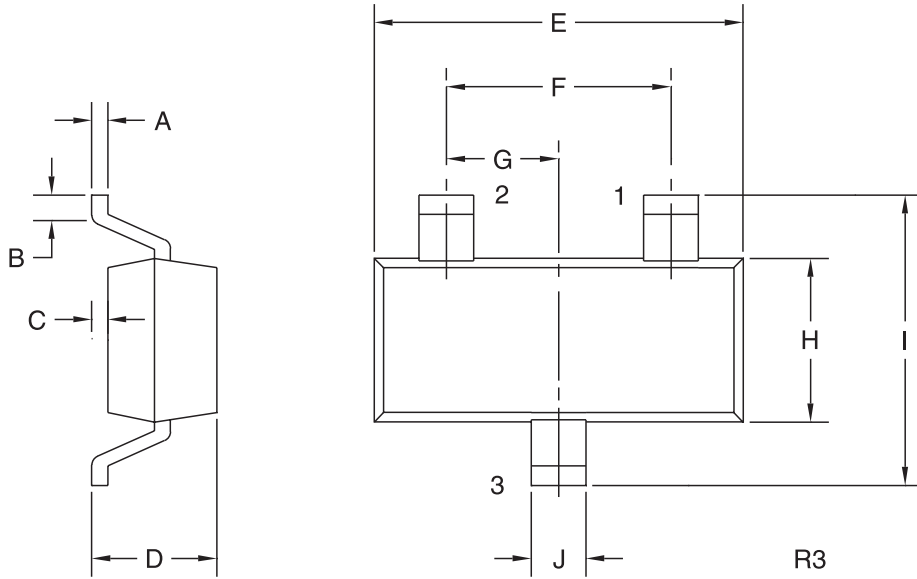
SYMBOL		UNITS
V _{CBO}	160	V
V _{CEO}	150	V
V _{EBO}	5.0	V
I _C	600	mA
P _D	350	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =120V		50	nA
I _{CBO}	V _{CB} =120V, T _A =100°C		50	μA
I _{EBO}	V _{EB} =3.0V		50	nA
BV _{CBO}	I _C =100μA	160		V
BV _{CEO}	I _C =1.0mA	150		V
BV _{EBO}	I _E =10μA	5.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.2	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.5	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		1.0	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA		1.0	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	50		
h _{FE}	V _{CE} =5.0V, I _C =10mA	60	240	
h _{FE}	V _{CE} =5.0V, I _C =50mA	50		
f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		6.0	pF
h _{fe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	40	200	
N _F	V _{CE} =5.0V, I _C =250μA, R _S =1.0kΩ f=10Hz to 15.7kHz		8.0	dB

R5 (29-May 2009)

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: C2L

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)